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Lee et al.

(10) **Pub. No.: US 2003/0090613 A1**(43) **Pub. Date:****May 15, 2003**(54) **LIQUID CRYSTAL DISPLAY DEVICE AND METHOD OF MANUFACTURING THEREOF**(52) **U.S. Cl. 349/141**(76) **Inventors:** Jae Kyun Lee, Anyang-shi (KR);
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(57)

ABSTRACT

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MCKENNA LONG & ALDRIDGE LLP**Teresa M. Arroyo****1900 K. Street, N.W.****Washington, DC 20006 (US)**(21) **Appl. No.:** 10/277,815(22) **Filed:** Oct. 23, 2002**Related U.S. Application Data**(63) Continuation of application No. 09/348,704, filed on
Jul. 7, 1999, now Pat. No. 6,509,939.(30) **Foreign Application Priority Data**

Jul. 7, 1998 (KR) 1998-27249

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A hybrid switching mode liquid crystal display device according to the present invention comprises first and second substrates, a gate bus line and a transparent data bus line defining unit pixel region, a common line parallel to a gate bus line in the pixel region, a TFT on the cross of a data bus line and the gate bus lines in the pixel region, a common electrode and a storage capacitor line in the pixel region, a gate insulator having holes on the gate bus line, the common electrode, and the storage capacitor lines, a passivation layer having holes on the gate insulator, a first alignment layer with a fixed alignment direction on the passivation layer, at least one counter electrode on the second substrate applying vertical and inclined electric fields with the common and data electrodes on the first substrate, a black matrix on the counter electrodes to prevent light leakage which may be generated around TFT, the gate bus lines, and the data bus lines, a color filter layer on the black matrix and the second substrate, a second alignment layer on the color filter layer, and a liquid crystal layer between the first and second substrates.

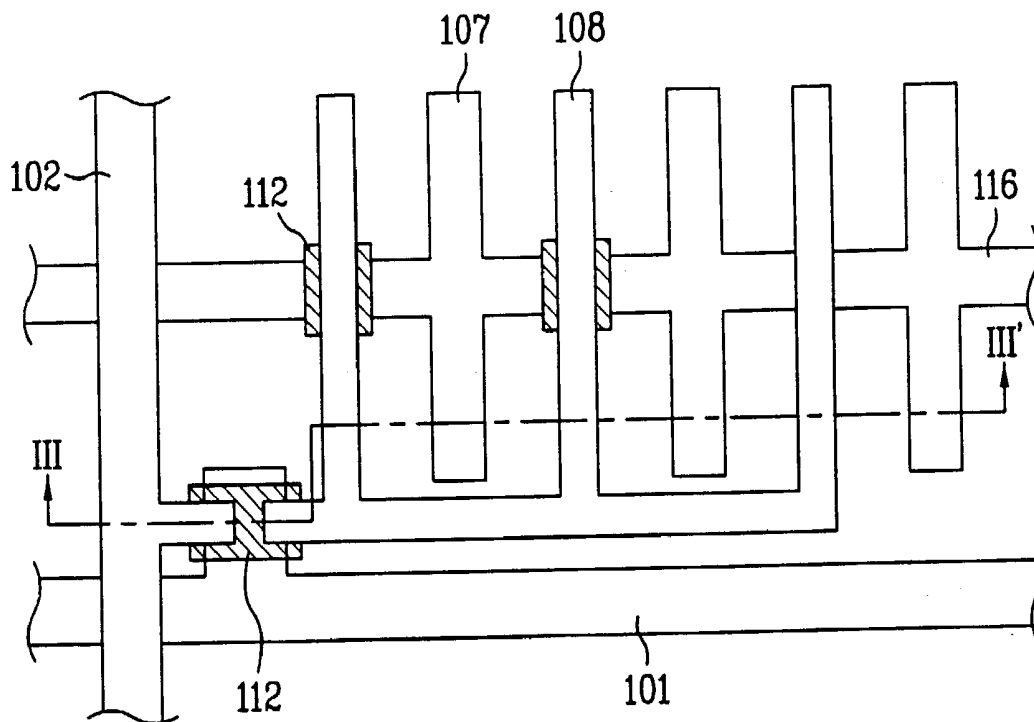


FIG. 1A
Prior Art

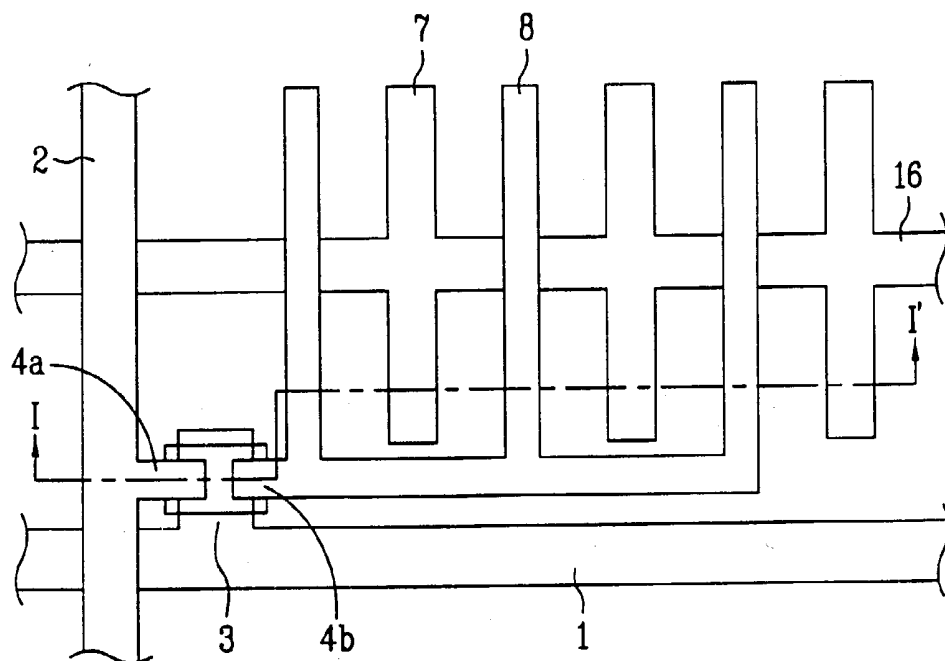


FIG. 1B
Prior Art

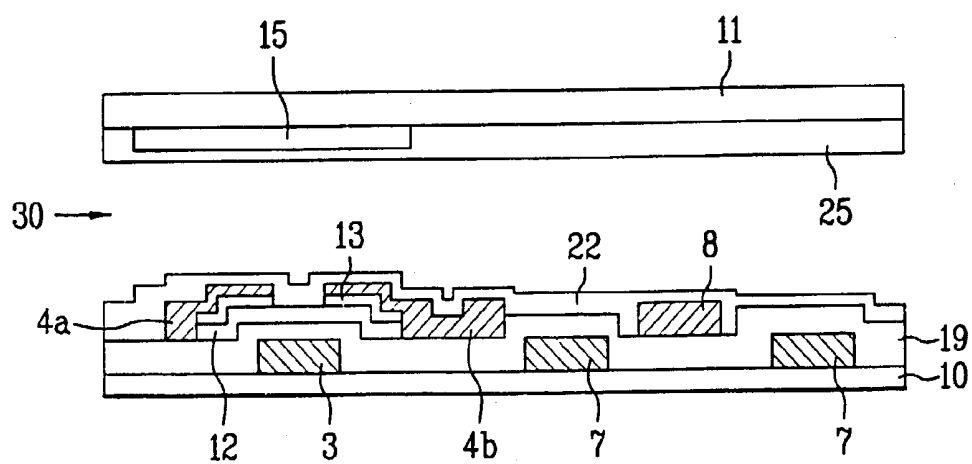


FIG. 2A
Prior Art

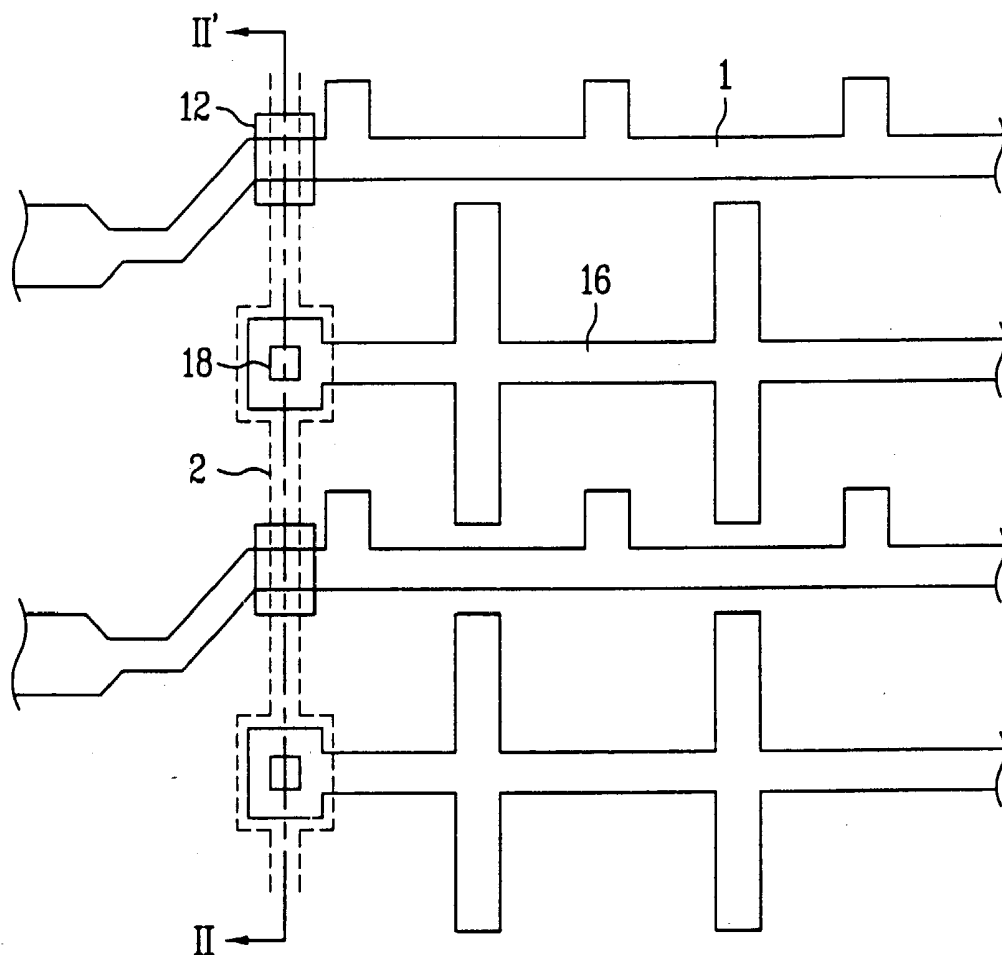


FIG. 2B
Prior Art

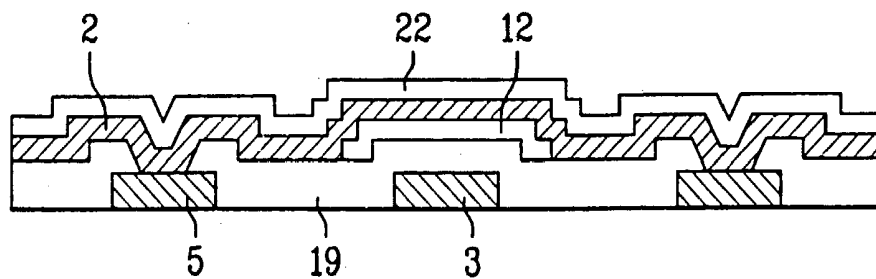


FIG. 3
Prior Art

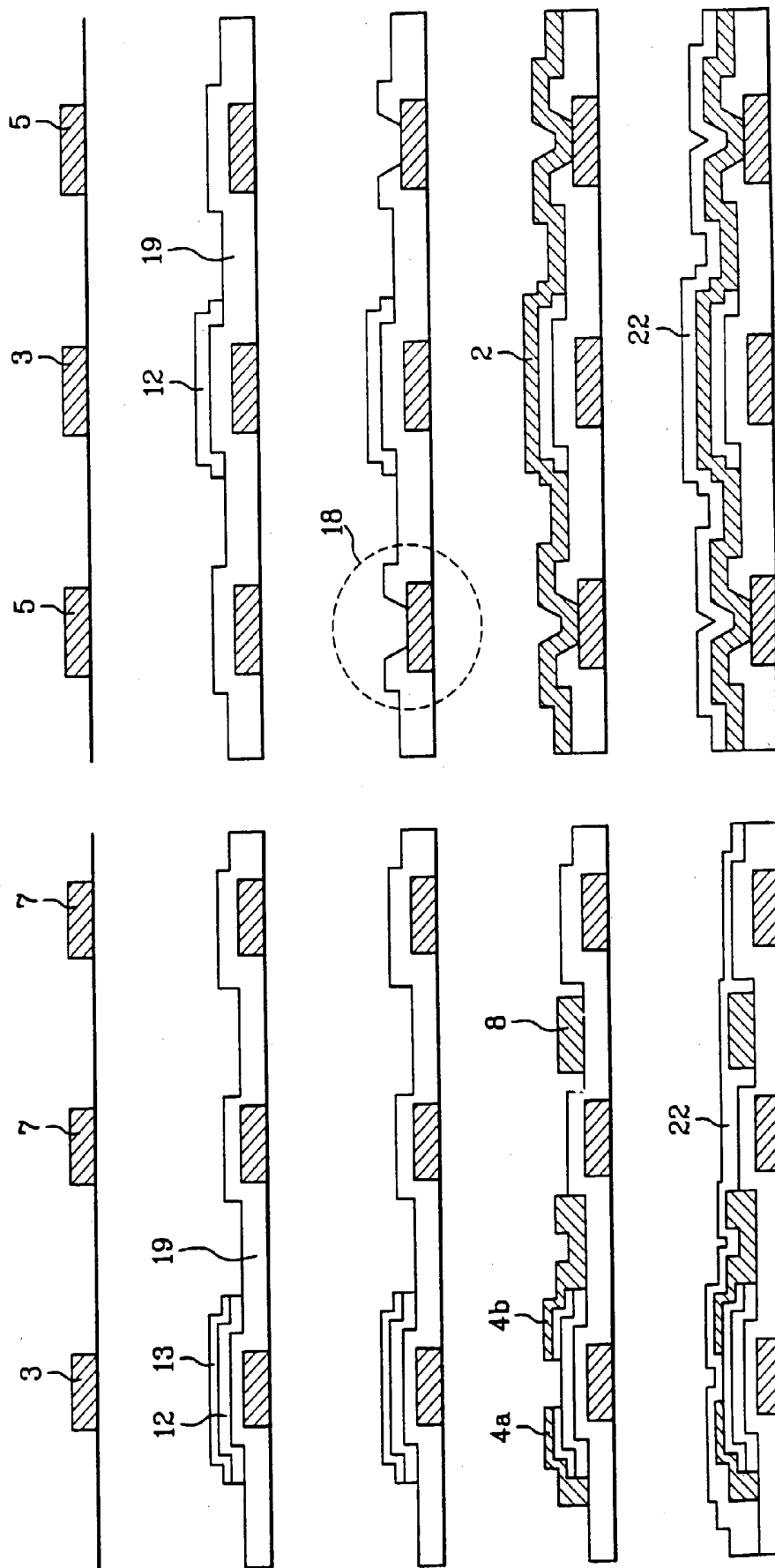


FIG. 5A

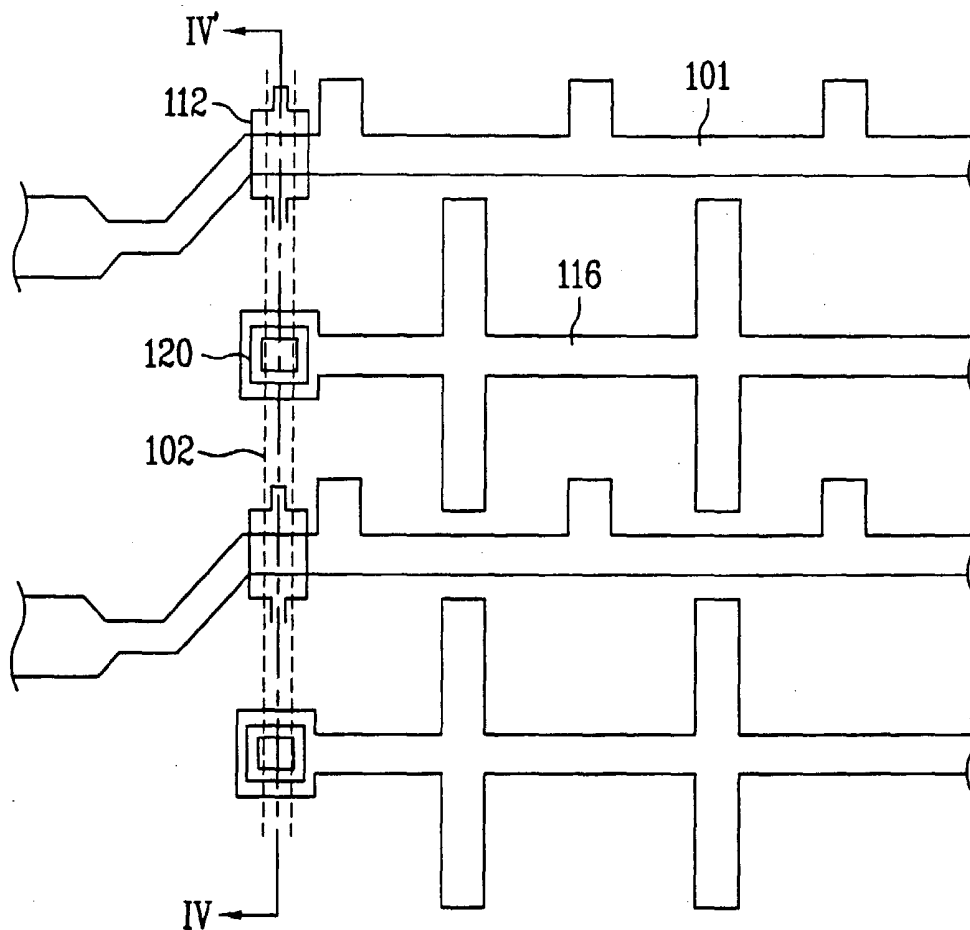


FIG. 5B

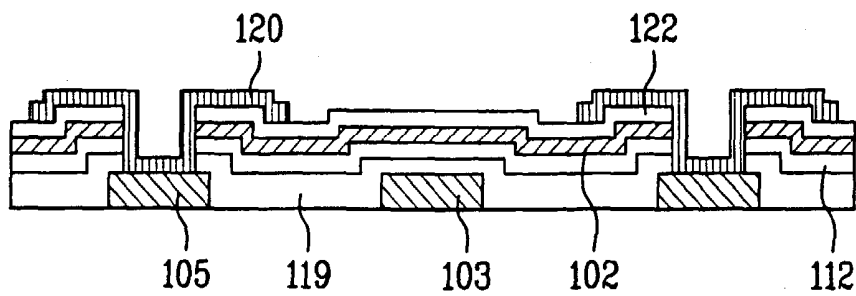


FIG. 5C

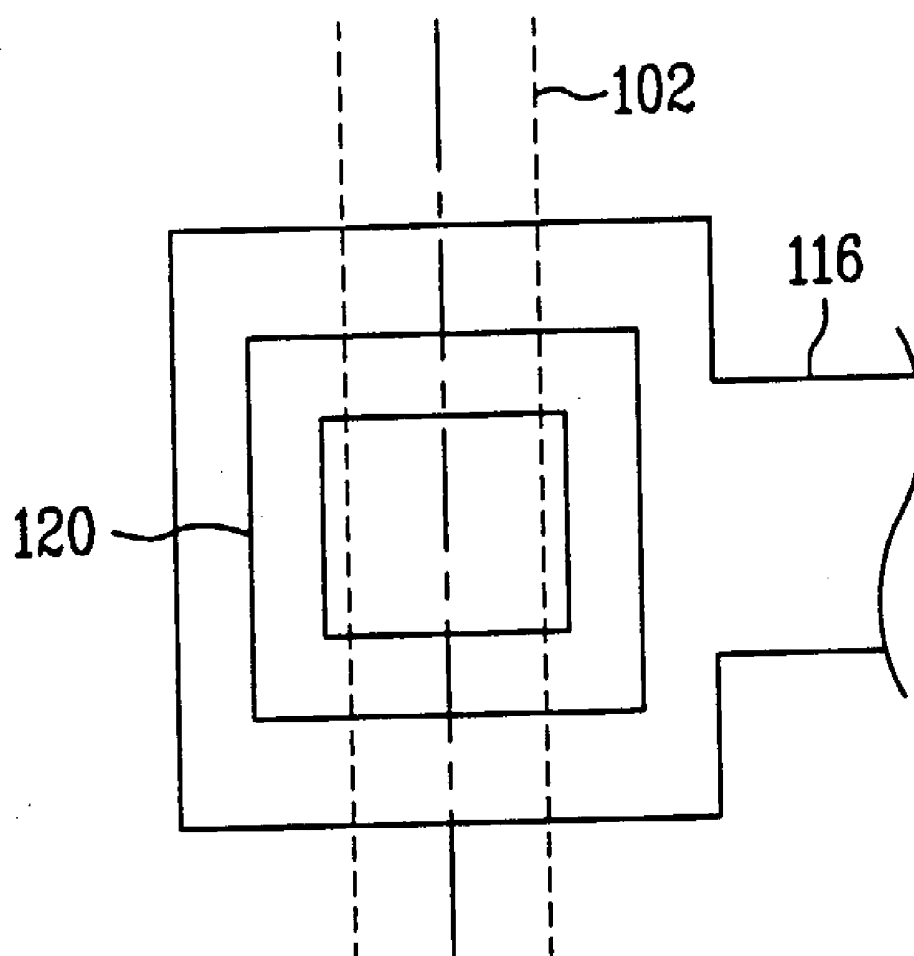


FIG. 6

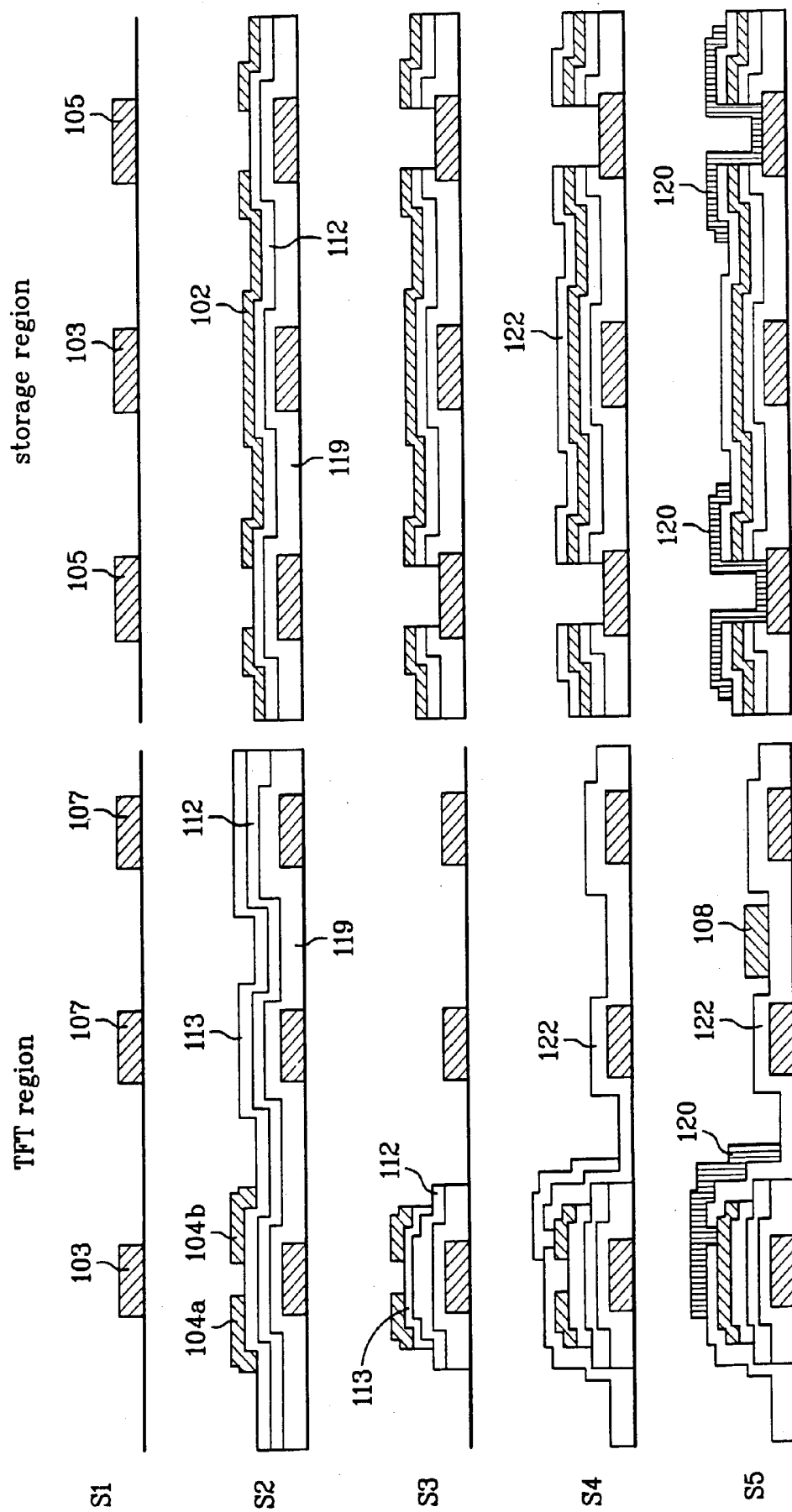
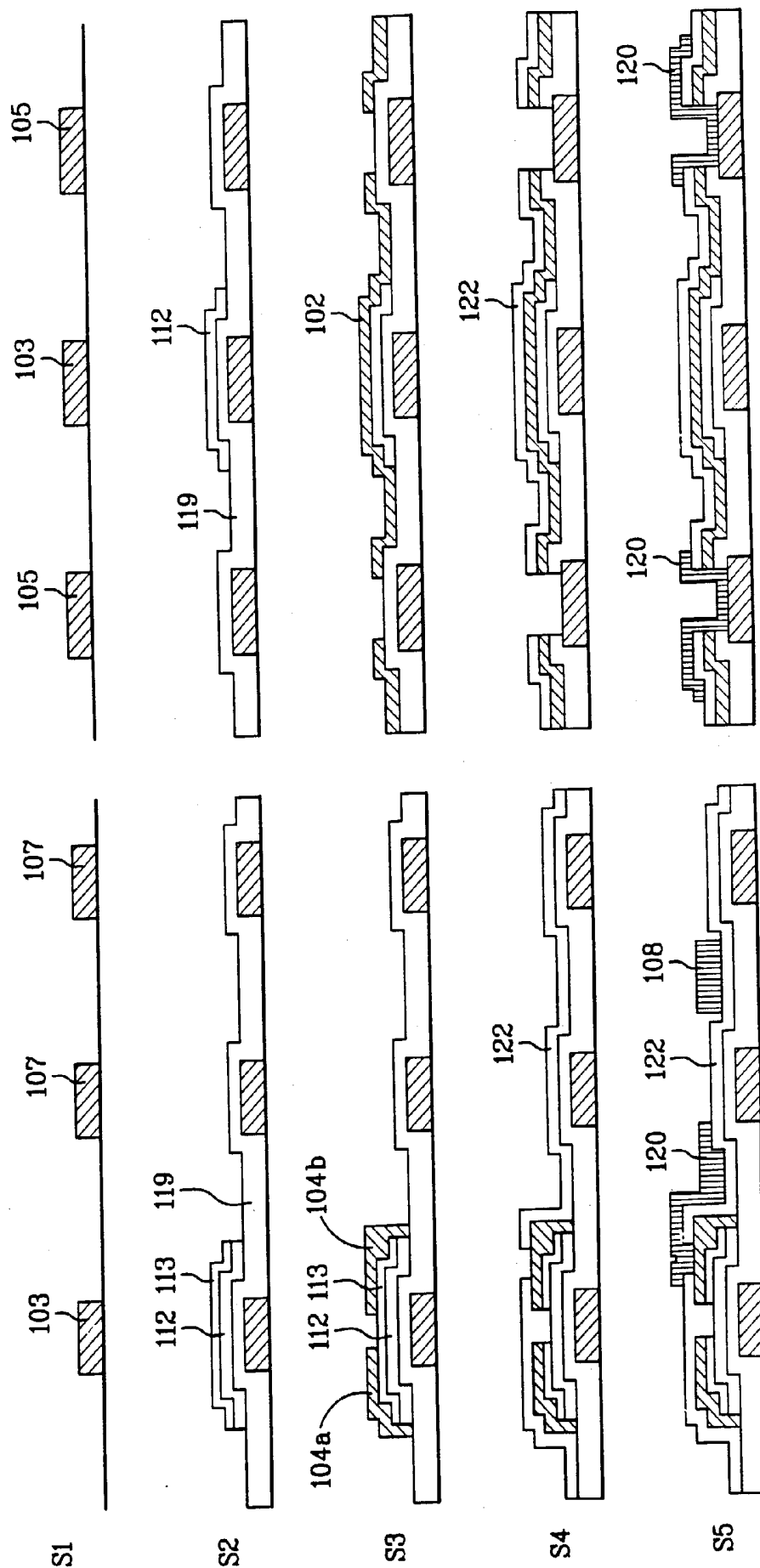


FIG. 7



LIQUID CRYSTAL DISPLAY DEVICE AND METHOD OF MANUFACTURING THEREOF

[0001] This application claims the benefit of Korean Patent Application No. 1998-27249, filed on Jul. 7, 1998, which is hereby incorporated by reference.

BACKGROUND OF THE INVENTION

[0002] 1. Field of Invention

[0003] The present invention relates to a liquid crystal display device and, more particularly, to a hybrid switching mode liquid crystal display device having a high aperture ratio and a method of manufacturing thereof.

[0004] 2. Discussion of Related Art

[0005] Since twisted nematic liquid crystal display devices (TN LCDs) have a high image quality and a low electric power consumption, they are widely applied to flat panel display device. TN LCDs, however, have a narrow viewing angle due to refractive anisotropic of liquid crystal molecules. This is caused by horizontally aligned liquid crystal molecules before voltage is applied are nearly vertically aligned with respect to a substrate when voltage is applied to a liquid crystal panel.

[0006] Recently, in-plane switching mode liquid crystal display devices (IPS-LCDs) are widely studied in which viewing angle characteristic is improved and these liquid crystal molecules are nearly horizontally aligned.

[0007] FIG. 1A is a plan view of a unit pixel of a conventional in-plane switching mode active matrix LCD. FIG. 1B is a sectional view according to line I-I' of FIG. 1A.

[0008] Referring to the drawings, an unit pixel region is defined by a gate bus line 1 and a data bus line 2 in which the lines are arranged perpendicularly and/or horizontally as a matrix shape on a first substrate 10. A common line 16 is arranged parallel to the gate bus line 1 in the pixel region and the thin film transistor (TFT) is formed on a cross of the data bus line 2 and the gate bus line 1. The TFT includes a gate electrode 3, a gate insulator 19, a semiconductor layer 12, an ohmic contact layer 13, and source/drain electrodes 4a, 4b in which the gate electrode 3 is connected to the gate bus line 1, and source/drain electrodes 4a, 4b are connected to the data bus line 2, and the gate insulator 19 is formed on the entire surface of the first substrate 10.

[0009] A common electrode 7 and a data electrode 8 are formed in the pixel region. The common electrode 7 is formed with the gate electrode 3 and connected to the common line 16, and the data electrode 8 is formed with the source/drain electrodes 4a, 4b and electrically connected to them. Further, a passivation layer 22 and a first alignment layer (not illustrated) are deposited on the entire surface of the first substrate 10.

[0010] On a second substrate 11, a black matrix 15 is formed to prevent a light leakage which may be generated around a TFT, the gate bus line 1, and the data bus line 2. A color filter layer 25, and a second alignment layer (not illustrated) is formed on the black matrix 15 in sequence. Also, a liquid crystal layer 30 is formed between the first and second substrates 10, 11.

[0011] When voltage is not applied to LCD having the above structure, liquid crystal molecules in the liquid crystal

layer 30 are aligned according to alignment directions of the first and second alignment layers, but when voltage is applied between the common electrode 7 and the data electrode 8, the liquid crystal molecules are aligned parallel to extending directions of the common and data electrode. As the foregoing, since liquid crystal molecules in the liquid crystal layer 30 are switched on the same plane at all times, grey inversion is not created in the viewing angle directions of up and down, and right and left directions.

[0012] FIG. 2A is a plan view of the part forming the storage capacitor line of the conventional LCD. FIG. 2B is a sectional view according to line II-II' of FIG. 2A.

[0013] Referring to the drawings, the gate insulator 19 and the semiconductor layer 12 are deposited on the gate electrode 3 and a storage capacitor line 5. The data bus line 2 is coupled to the storage capacitor line 5 through a hole 18 of the gate insulator 19 and formed with the source/drain electrodes 4a, 4b of FIG. 1A. A method for manufacturing the LCD having above structure is described in FIG. 3.

[0014] A TFT region describes a sectional region according to line I-I' of FIG. 1A, and a storage region describes a sectional region according to line II-II' of FIG. 2A.

[0015] As shown in the drawing, a method of manufacturing the conventional LCD comprises the steps of patterning the gate electrode 8, the common electrode 7, and the storage capacitor line 5 (S1), patterning the semiconductor layer 12 and the ohmic contact layer 13 after forming the gate insulator 19, the semiconductor layer 12, and the ohmic contact layer 13 on the gate electrode 3 (S2), forming the hole 18 by opening some part of the gate insulator 19 in the part forming the storage capacitor line 5 (S3), patterning the source/drain electrodes 4a, 4b, the data electrode 8, and the data bus line 2 on the ohmic contact layer 13 and the gate insulator 19 (S4), forming the passivation layer 22 after n⁺ dry etching (S5).

[0016] However, in the conventional LCD, it is necessary that each of the storage capacitor lines and pad open regions are formed respectively, and the storage capacitor lines are coupled to each other by the data bus line when the gate insulator is patterned to form the storage capacitor line.

SUMMARY OF THE INVENTION

[0017] An object of the present invention is to provide a hybrid switching mode LCD having a high opening ratio due to transparent connecting parts for connecting to an outer driving circuit by etching a passivation layer/pad at the same time thereby forming a storage capacitor line, and a method of manufacturing thereof.

[0018] Additional features and advantages of the invention will be set forth in the description which follows, and in part will be apparent from the description, or may be learned by practice of the invention. The objectives and other advantages of the invention will be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

[0019] To achieve the above object, a hybrid switching mode LCD according to the present invention comprises first and second substrates, transparent data bus lines and gate bus lines defining a pixel region on the first substrate in

which the lines are arranged perpendicularly and/or horizontally as a matrix shape, especially the transparent data bus lines made of, for example, ITO (indium tin oxide) has holes, common lines formed parallel to the gate bus lines in the pixel region, TFTs on the cross of the data bus lines and the gate bus lines in the pixel region, common electrodes and storage capacitor lines in pixel region, a gate insulator having holes on the gate bus lines, the common electrodes, and the storage capacitor lines, a passivation layer having holes on the gate insulator, a first alignment layer with a fixed alignment direction on the passivation layer, at least one counter electrode on the second substrate thereby applying vertical and inclined electric fields with the common and data electrodes on the first substrate, black matrixes on the counter electrodes to prevent a light leakage which may be generated around TFTs, the gate bus lines, and the data bus lines, a color filter layer on the black matrix and the second substrate, a second alignment layer on the color filter layer, and a liquid crystal layer between the first and second substrates.

[0020] A method of manufacturing the above LCD comprises the steps of forming the gate bus lines, the gate electrodes, the common lines, and the storage capacitor lines, depositing an inorganic material, an amorphous silicon, and an impurity amorphous silicon, forming source/drain electrodes and the data electrodes by patterning a metal, forming the gate insulator and the semiconductor layers having holes by etching the inorganic material and amorphous silicon with masks of source/drain electrodes and the metal, forming an ohmic contact layer by etching the impurity amorphous silicon, forming the passivation layer by patterning an organic material or an inorganic material, depositing a transparent metal layer such as ITO for storage capacitor on the gate insulator, the semiconductor layers, and the metal lines, depositing the first alignment layer, forming at least one counter electrode on the second substrate thereby applying vertical and inclined electric fields with the common and data electrodes on the first substrate, forming the black matrixes on the counter electrode, forming a color filter layer on the black matrix and the second substrate, forming the second alignment layer on the color filter layer, and forming the liquid crystal layer between the first and second substrates.

[0021] According to another embodiment of the present invention, after forming the gate insulator, the semiconductor layer is patterned and the source/drain electrodes are formed. After that, the passivation layer is deposited after forming the ohmic contact layer by n+ dry etching the impurity amorphous silicon with the mask of the source/drain electrodes. Further, after forming the holes by etching the passivation/pad at the same time, transparent connecting parts for connecting to an outer driving circuit and transparent common electrodes are formed on the holes.

[0022] It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are intended to provide a further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0023] The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this specification,

illustrate embodiments of the invention, and together with the description, serve to explain the principles of the invention.

[0024] FIG. 1A is a plan view of a unit pixel of a conventional in-plane switching mode active matrix LCD, and FIG. 1B is a sectional view according to line I-I' of FIG. 1A;

[0025] FIG. 2A is a plan view of the part forming the storage capacitor line of the conventional LCD, and FIG. 2B is a sectional view according to line II-II' of FIG. 2A;

[0026] FIG. 3 is a drawing showing a method for manufacturing the conventional LCD;

[0027] FIG. 4A is a plan view of a unit pixel of a hybrid switching mode active matrix LCD according to the present invention;

[0028] FIG. 4B is a sectional view according to line III-III' of FIG. 4A;

[0029] FIG. 5A is a plan view of the part forming the storage capacitor line of the present invention;

[0030] FIG. 5B is a sectional view according to line IV-IV' of FIG. 5A;

[0031] FIG. 5C is a partial plan view of FIG. 5A;

[0032] FIG. 6 is a drawing showing a method according to a first embodiment of the present invention; and

[0033] FIG. 7 is a drawing showing a method according to a second embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0034] Hereinafter, preferred embodiments of the present invention will be described in detail in reference to the accompanying drawings.

[0035] FIG. 4A is a plan view of a unit pixel of a hybrid switching mode active matrix LCD according to the present invention. FIG. 4B is a sectional view according to line III-III' of FIG. 4A. As shown in the drawings, a gate bus line 101 and a transparent data bus line 102 defining pixel region are arranged perpendicularly and/or horizontally as matrix shape on the first substrate 110, common line 116 is formed parallel to the gate bus line 101, TFT is formed on a cross of the data bus line 102 and the gate bus line 101 in pixel region, a gate electrode 103 of TFT is coupled to the gate bus line 101 and a source electrode 104a is coupled to the data bus line 102. In the pixel region, a common electrode 107 and a data electrode 108 are formed parallel to each other. The common electrode 107 is coupled to the common line 116 and the data electrode 108 is coupled to a drain electrode 104b through a transparent metal layer 120.

[0036] Although not shown in the drawing, it is possible that the two electrodes 107, 108 are formed on a single layer. Namely, the two electrodes 107, 108 are formed on a gate insulator 119 on the first substrate 110. The common line 116 and the common electrode 107 are formed on the gate insulator 119 or a passivation layer 122 through holes thereon.

[0037] A semiconductor layer 112 is formed to prevent a short which is generated between the common line 116 and

the data electrode **108** and on a cross point of the gate bus line **101** and the data bus line **102**. In addition, a first alignment layer (not illustrated) is formed on the passivation layer **122**.

[0038] On the second substrate **111**, at least one counter electrode **123** applying vertical and inclined electric fields with the common and data electrodes **107**, **108** is formed. A black matrix **115** for preventing light leakage, which may be generated around TFTs, the gate bus lines, and the data bus lines, is formed on the counter electrodes. A color filter layer **125** including color filter elements of R, G, and B is formed on the black matrix **115**. A second alignment layer (not illustrated) is formed on the color filter layer **125**. A liquid crystal layer is formed between the first and second substrates.

[0039] Between the color filter layer **125** and the second alignment layer, an overcoat layer may be formed. Further, the black matrix may function as a common electrode.

[0040] FIG. 5A is a plan view of the part forming the storage capacitor line of FIG. 4A. FIG. 5B is a sectional view according to line IV-IV' of FIG. 5A. FIG. 5C is a partial plan view of FIG. 5A. Referring to the drawings, the gate insulator **119**, the semiconductor layer **112**, and the data bus line **102** are deposited on the gate electrode **103** and a storage capacitor line **105**. At this time, the data bus line **102** is formed with source/drain electrodes **4a**, **4b** of FIG. 4A and the passivation layer **122** is formed thereon. In addition, on the data bus line **102**, the transparent metal layer **120** connecting the data bus line **102** to the storage capacitor line **105** is formed on the data bus line **102**. The passivation layer **122** may be formed on the TFT region only to achieve a strong electric field.

[0041] FIG. 6 is a drawing showing a method according to a first embodiment of the present invention. Referring to the drawing, the TFT region describes a sectional region according to line III-III' of FIG. 4A, and the storage region describes a sectional region according to line IV-IV' of FIG. 5A. As shown in the drawing, firstly, the gate electrode **103**, the common electrode **107**, and the storage capacitor line **105** are formed by depositing and etching a metal such as Ta, Al, Cr, Mo, or Al alloy using a sputtering method (S1). Although not shown in the drawing, the gate bus line and the common line are formed at the same time. At this time, it is possible to form an anodic oxidation layer by anodizing the gate electrode **103** and the common electrode **107** to improve the insulating characteristic.

[0042] The source/drain electrodes **104a**, **104b** are formed after depositing an inorganic material such as SiNx or SiOx, an amorphous silicon, and an impurity amorphous silicon by PCVD (plasma chemical vapor deposition) method, and patterning the data bus line **102** in order to have holes (S2). The ohmic contact layer **113** is formed continually by patterning the gate insulator **119** and the semiconductor layer **112** with masks of the data bus line **102** and the source/drain electrodes **104a**, **104b**, and etching the impurity amorphous silicon layer (S3). After the passivation layer **122** is formed by depositing and etching an inorganic material such as SiNx or SiOx, or an organic material such as BCB (benzocyclobutene) (S4), the storage capacitor line **105** and the data bus line **102** are coupled to each other electrically by depositing a transparent metal such as ITO on the holes of the gate insulator **119**, the semiconductor layer **112**, and

the data bus line **102** (S5). Further more, an etch stopper may be formed on the semiconductor layer **112** to prevent channel region from etching. The first alignment layer (not illustrated) is formed on the passivation layer **122**.

[0043] On the second substrate **111**, although not shown in the drawing, at least one counter electrode applying vertical and inclined electric fields with the common and data electrodes **107**, **108** is formed. The black matrix for preventing light leakage, which may be generated around TFTs, the gate bus lines, and the data bus lines, a color filter layer, and a second alignment layer, are formed in sequence, and in a liquid crystal layer formed between the first and second substrates.

[0044] Each alignment direction of the first and second alignment layers is determined by a rubbing method using polyamide, polyimide, SiO₂, PVA (polyvinylalcohol) or polyamic acid, or by a photo-alignment method using photosensitive material such as PVCN (polyvinylcinnamate), PSCN (polysiloxanecinnamate) or CelCN (cellulosecinnamate).

[0045] FIG. 7 is a drawing showing a method according to a second embodiment of the present invention. The difference between the first embodiment and the second embodiment is that the gate insulator is formed on the entire surface of the first substrate and the semiconductor layer is patterned selectively.

[0046] Referring to the drawing, a TFT region describes a sectional region according to line III-III' of FIG. 4A, and a storage region describes a sectional region according to line IV-IV' of FIG. 5A.

[0047] As shown in the drawings, firstly, the gate electrode **103**, the common electrode **107**, and the storage capacitor line **105** are formed by depositing and etching a metal such as Ta, Al, Cr, Mo, or Al alloy using a sputtering method (S1). Although not shown in the drawing, the gate bus line and the common line are formed at the same time. At this time, it is possible to form an anodic oxidation layer by anodizing the gate electrode **103** and the common electrode **107** to improve the insulating characteristic.

[0048] The gate insulator **119** is formed on the entire surface of the first substrate **110** by depositing an inorganic material such as SiNx or SiOx, and the semiconductor layer **112** and the ohmic contact layer **113** are formed by depositing and patterning an amorphous silicon, and an impurity amorphous silicon by PCVD (plasma chemical vapor deposition) method (S2).

[0049] The source/drain electrodes **104a**, **104b** and the data bus line **102** are patterned (S3). The passivation layer **122** is formed continually by depositing and etching an inorganic material such as SiNx or SiOx, or an organic material such as BCB (benzocyclobutene) with masks of the source/drain electrodes **104a**, **104b** after n+ dry etching the ohmic contact layer **113** (S4).

[0050] After forming the passivation layer **122**, the storage capacitor line **105** and the data bus line **102** are coupled to each other electrically by depositing a transparent metal such as ITO on the holes of the gate insulator **119**, the semiconductor layer **112**, and the data bus line **102** (S5). At this time, some part of the passivation layer **122** and the gate insulator **119** on the storage region are etched at the same time.

[0051] According to the present invention, it is possible to obtain a hybrid switching mode LCD having a high opening

ratio due to transparent connecting parts for connecting to an outer driving circuit by etching a passivation layer/pad at the same time thereby forming a storage capacitor line.

[0052] It will be apparent to those skilled in the art that various modifications and variations can be made in the present invention without departing from the spirit or scope of the invention. Thus, it is intended that the present invention cover the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. A hybrid switching mode liquid crystal display device comprising:

- first and second substrates;
- a plurality of gate and transparent data bus lines defining pixel regions and arranged perpendicularly and/or horizontally on said first substrate;
- a common line parallel to said gate bus line;
- a plurality of thin film transistors formed on cross points of said gate and data bus lines;
- at least one pair of common electrode and transparent data electrode;
- a plurality of storage capacitor lines on a plane of said common electrode;
- a passivation layer on said first substrate;
- a transparent metal layer for connecting said data bus lines to said storage capacitor lines;
- at least one counter electrode on said second substrate to apply vertical and inclined electric fields with said common and data electrodes;
- a liquid crystal layer between said first substrate and said second substrate; and
- at least one alignment layer on said two substrates.

2. The hybrid switching mode liquid crystal display device according to claim 1, wherein each of thin film transistors includes a gate electrode connected to said gate bus line and said common electrode, a gate insulator having a contact hole on said gate electrode, a semiconductor layer having a contact hole on said gate insulator, an ohmic contact layer on said semiconductor layer, and source/drain electrodes on said ohmic contact layer.

3. The hybrid switching mode liquid crystal display device according to claim 1, wherein said transparent metal layer includes indium tin oxide.

4. The hybrid switching mode liquid crystal display device according to claim 1, wherein said counter electrode for preventing a light leakage being generated around said thin film transistors, said gate bus lines, and said data bus lines.

5. A method of manufacturing a hybrid switching mode liquid crystal display device, the method comprising the steps of:

- providing first and second substrates;
- forming a gate bus line, a gate electrode, a common line, a common electrode, and a storage capacitor line by depositing and etching a metal;

continually depositing an inorganic material, an amorphous silicon, and an impurity amorphous silicon;

forming source/drain electrodes and a data electrode on said continually deposited layers;

forming a gate insulator and a semiconductor layer having holes by etching said inorganic material and amorphous silicon with masks of said source/drain electrodes and said metal;

forming an ohmic contact layer by etching said impurity amorphous silicon;

forming a passivation layer by patterning an organic material or an inorganic material;

forming a transparent metal layer for storage capacitor on said gate insulator, said semiconductor layer, and said metal line; and

forming a first alignment layer on said first substrate.

6. The method of according to claim 5, further comprising the steps of:

forming at least one counter electrode on said second substrate to apply vertical and inclined electric fields with said common and data electrodes;

forming a black matrix on said counter electrode;

forming a color filter layer on said black matrix and the second substrate;

forming a second alignment layer on said color filter layer; and

forming a liquid crystal layer between said first and second substrates.

7. The method of according to claim 5, wherein said transparent metal layer includes indium tin oxide.

8. The method of according to claim 6, wherein said counter electrode for preventing a light leakage being generated around said thin film transistor, said gate bus line, and said data bus line.

9. A method of manufacturing a hybrid switching mode liquid crystal display device, the method comprising the steps of:

providing first and second substrates;

forming a gate bus line, a gate electrode, a common line, a common electrode, and a storage capacitor line by depositing and etching a metal;

continually depositing an inorganic material, an amorphous silicon, and an impurity amorphous silicon;

forming a semiconductor layer and an ohmic contact layer by etching said amorphous silicon and impurity amorphous silicon;

forming source/drain electrodes and a data electrode on said continually deposited layers;

forming a passivation layer on said first substrate;

forming a transparent data electrode on said passivation layer; and

forming a first alignment layer on said first substrate.

10. The method of according to claim 9, further comprising the steps of:

forming at least one counter electrode on said second substrate to apply vertical and inclined electric fields with said common and data electrodes;

forming a black matrix on said counter electrode;

forming a color filter layer on said black matrix and the second substrate;

forming a second alignment layer on said color filter layer; and

forming a liquid crystal layer between said first and second substrates.

11. The method of according to claim 9, wherein said step of forming a passivation layer includes the steps of depositing and etching an organic material or an inorganic material.

12. The method of according to claim 9, wherein said data electrode includes indium tin oxide.

* * * * *

专利名称(译)	液晶显示装置及其制造方法		
公开(公告)号	US20030090613A1	公开(公告)日	2003-05-15
申请号	US10/277815	申请日	2002-10-23
[标]申请(专利权)人(译)	李在筠 韩昌旭		
申请(专利权)人(译)	李在筠 韩昌旭		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	LEE JAE KYUN HAN CHANG WOOK		
发明人	LEE, JAE KYUN HAN, CHANG WOOK		
IPC分类号	G02F1/136 G02F1/1343		
CPC分类号	G02F2001/134381 G02F1/134363		
优先权	1019980027249 1998-07-07 KR		
其他公开文献	US6833881		
外部链接	Espacenet USPTO		

摘要(译)

根据本发明的混合开关模式液晶显示装置包括第一和第二基板，栅极总线和限定单元像素区域的透明数据总线，与像素区域中的栅极总线平行的公共线，TFT在像素区域中的数据总线和栅极总线的交叉处，像素区域中的公共电极和存储电容器线，在栅极总线上具有孔的栅极绝缘体，公共电极和存储电容器线，在栅极绝缘体上具有孔的钝化层，在钝化层上具有固定取向方向的第一取向层，在第二基板上的至少一个对电极施加垂直和倾斜电场，在第一基板上具有公共电极和数据电极基板，对电极上的黑色矩阵，以防止可能在TFT，栅极总线 and 数据总线周围产生的漏光，b上的滤色层缺少基质和第二基板，滤色器层上的第二取向层，以及第一和第二基板之间的液晶层。

